

CY2310BNZ

3.3V SDRAM Buffer for Mobile PCs with 4 SO-DIMMs

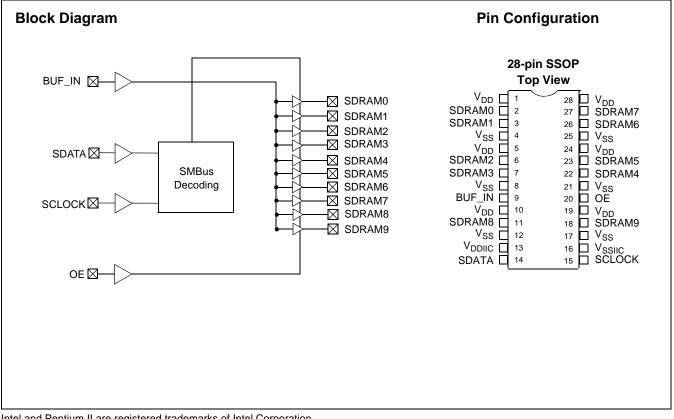
Features

- · One input to 10 output buffer/driver
- Supports up to four SDRAM SO-DIMMs
- Two additional outputs for feedback
- SMBus interface for output control
- · Low skew outputs
- Up to 100 MHz operation
- Multiple V_{DD} and V_{SS} pins for noise reduction
- · Dedicated OE pin for testing
- Space-saving 28-pin SSOP package
- 3.3V operation

Functional Description

The CY2310BNZ is a 3.3V buffer designed to distribute high-speed clocks in mobile PC applications. The part has 10 outputs, 8 of which can be used to drive up to four SDRAM SO-DIMMs, and the remaining can be used for external feedback to a PLL. The device operates at 3.3V and outputs can run up to 100 MHz, thus making it compatible with Pentium II® processors. The CY2310BNZ can be used in conjunction with the CY2281 or similar clock synthesizer for a full Pentium II motherboard solution.

The CY2310BNZ also includes an SMBus interface which can enable or disable each output clock. On power-up, all output clocks are enabled. A separate Output Enable pin facilitates testing on ATE.



Intel and Pentium II are registered trademarks of Intel Corporation.

San Jose



Pin Summary

| Name | Pins | Description |
|--------------------|----------------------|--|
| V _{DD} | 1, 5, 10, 19, 24, 28 | 3.3V Digital voltage supply |
| V _{SS} | 4, 8, 12, 17, 21, 25 | Ground |
| V _{DDIIC} | 13 | SMBus Voltage supply |
| V _{SSIIC} | 16 | Ground for SMBus |
| BUF_IN | 9 | Input clock |
| OE | 20 | Output Enable, three-states outputs when LOW. Internal pull-up to V_{DD} |
| SDATA | 14 | SMBus data input, internal pull-up to V _{DD} |
| SCLK | 15 | SMBus clock input, internal pull-up to V _{DD} |
| SDRAM [0-3] | 2, 3, 6, 7 | SDRAM byte 0 clock outputs |
| SDRAM [4-7] | 22, 23, 26, 27 | SDRAM byte 1 clock outputs |
| SDRAM [8–9] | 11, 18 | SDRAM byte 2 clock outputs |

Device Functionality

| OE | SDRAM [0–17] |
|----|--------------|
| 0 | High-Z |
| 1 | 1 x BUF_IN |

Serial Configuration Map

• The Serial bits will be read by the clock driver in the following order:

Byte 0 - Bits 7, 6, 5, 4, 3, 2, 1, 0 Byte 1 - Bits 7, 6, 5, 4, 3, 2, 1, 0

.

- Byte N Bits 7, 6, 5, 4, 3, 2, 1, 0
- Reserved and unused bits should be programmed to "0".

• SMBus Address for the CY2310BNZ is:

| Γ | A6 | A5 | A4 | A3 | A2 | A1 | A0 | R/W |
|---|----|----|----|----|----|----|----|-----|
| | 1 | 1 | 0 | 1 | 0 | 0 | 1 | |

Byte 0:SDRAM Active/Inactive Register (1 = Enable, 0 = Disable), Default = Enabled

| Bit | Pin # | Description |
|-------|-------|--------------------------|
| Bit 7 | | Initialize to 0 |
| Bit 6 | | Initialize to 0 |
| Bit 5 | | Initialize to 0 |
| Bit 4 | | Initialize to 0 |
| Bit 3 | 7 | SDRAM3 (Active/Inactive) |
| Bit 2 | 6 | SDRAM2 (Active/Inactive) |
| Bit 1 | 3 | SDRAM1 (Active/Inactive) |
| Bit 0 | 2 | SDRAM0 (Active/Inactive) |

Byte 1: SDRAM Active/Inactive Register (1 = Active, 0 = Inactive), Default = Active

| Bit | Pin # | Description |
|-------|-------|--------------------------|
| Bit 7 | 27 | SDRAM7 (Active/Inactive) |
| Bit 6 | 26 | SDRAM6 (Active/Inactive) |
| Bit 5 | 23 | SDRAM5 (Active/Inactive) |
| Bit 4 | 22 | SDRAM4 (Active/Inactive) |
| Bit 3 | | Initialize to 0 |
| Bit 2 | | Initialize to 0 |
| Bit 1 | | Initialize to 0 |
| Bit 0 | | Initialize to 0 |

Byte 2: SDRAM Active/Inactive Register (1 = Active, 0 = Inactive), Default = Active

| Bit | Pin # | Description |
|-------|-------|--------------------------|
| Bit 7 | 18 | SDRAM9 (Active/Inactive) |
| Bit 6 | 11 | SDRAM8 (Active/Inactive) |
| Bit 5 | | Reserved, drive to 0 |
| Bit 4 | | Reserved, drive to 0 |
| Bit 3 | | Reserved, drive to 0 |
| Bit 2 | | Reserved, drive to 0 |
| Bit 1 | | Reserved, drive to 0 |
| Bit 0 | | Reserved, drive to 0 |



Maximum Ratings

| Supply Voltage to Ground Potential0.5V to +7.0V |
|--|
| DC Input Voltage (Except BUF_IN)–0.5V to $\rm V_{DD}$ + 0.5V |
| DC Input Voltage (BUF_IN)0.5V to +7.0V |

| Storage Temperature | . –65°C to +150°C |
|--------------------------------|-------------------|
| Static Discharge Voltage | |
| (per MIL-STD-883, Method 3015) | >2000V |
| Ambient Temperature under BIAS | . –55°C to +125°C |

Operating Conditions

| Parameter | Description | Min. | Max. | Unit |
|-----------------|---|-------|-------|------|
| V _{DD} | Supply Voltage | 3.135 | 3.465 | V |
| T _A | Operating Temperature (Ambient Temperature) | -40 | 85 | °C |
| CL | Load Capacitance | 20 | 30 | pF |
| C _{IN} | Input Capacitance | | 5 | pF |



Absolute Maximum Ratings

Stresses greater than those listed in this table may cause permanent damage to the device. These represent a stress rating only. Operation of the device at these or any other conditions above those specified in the operating sections of this specification is not implied. Maximum conditions for extended periods may affect reliability.

| Parameter | Description | Rating | Unit |
|-----------------------------------|--|--------------|------|
| V _{DD} , V _{IN} | Voltage on any Pin with Respect to GND | -0.5 to +7.0 | V |
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| T _A | Operating Temperature | 0 to +70 | °C |
| Т _В | Ambient Temperature under Bias | -55 to +125 | °C |

DC Electrical Characteristics: $T_A = -40$ °C to +85°C, $V_{DD} = 3.3V\pm5\%$

| Description | Test Condition/Comments | Min. | Тур. | Max. | Unit |
|---------------------------------------|---|---|---|--|--|
| 3.3V Supply Current | at 64MHz | 100 | 140 | 180 | mA |
| 3.3V Supply Current | at 100 MHz | 150 | 185 | 220 | mA |
| 3.3V Supply Current in Three-State | | | 5 | 10 | mA |
| : : | | • | | • | |
| Input Low Voltage | | V _{SS} -0.3 | | 0.8 | V |
| Input High Voltage | | 2.0 | | V _{DD} +0.5 | V |
| Input Leakage Current, BUF_IN | | -5 | | +5 | μA |
| Input Leakage Current ^[1] | | -20 | | +5 | μA |
| ts (SDRAM0:9) ^[2] | · | | | | |
| Output Low Voltage | I _{OL} = 1 mA | | | 50 | mV |
| Output High Voltage | I _{OH} = -1 mA | 3.1 | | | V |
| Output Low Current | V _{OL} = 1.5V | 70 | 110 | 185 | mA |
| Output High Current | V _{OH} = 1.5V | 65 | 100 | 160 | mA |
| ince/Inductance | · | | | | |
| Input Pin Capacitance | | | | 5 | pF |
| Output Pin Capacitance | | | | 6 | pF |
| Input Pin Inductance | | | | 7 | nH |
| | 3.3V Supply Current 3.3V Supply Current 3.3V Supply Current in Three-State Input Low Voltage Input High Voltage Input Leakage Current, BUF_IN Input Leakage Current ^[1] ts (SDRAM0:9) ^[2] Output Low Voltage Output High Voltage Output High Voltage Output High Current Output High Current Input Pin Capacitance Output Pin Capacitance | 3.3V Supply Current at 64MHz 3.3V Supply Current in at 100 MHz 3.3V Supply Current in Three-State Input Low Voltage Input High Voltage Input Leakage Current, BUF_IN Input Leakage Current ^[1] ts (SDRAM0:9) ^[2] $I_{OL} = 1 \text{ mA}$ Output Low Voltage $I_{OH} = -1 \text{ mA}$ Output High Voltage $I_{OH} = 1.5V$ Output High Current $V_{OH} = 1.5V$ Input Pin Capacitance Output Pin Capacitance | 3.3V Supply Currentat 64MHz1003.3V Supply Currentat 100 MHz1503.3V Supply Current in Three-State V_{SS} -0.3Input Low VoltageV_SS-0.3Input High Voltage2.0Input Leakage Current, BUF_IN-5Input Leakage Current[1]-20ts (SDRAM0:9) ^[2] $O_{L} = 1 \text{ mA}$ Output Low Voltage $I_{OL} = 1 \text{ mA}$ Output High Voltage $I_{OL} = 1.5V$ Output High Current $V_{OL} = 1.5V$ Output High Current $V_{OH} = 1.5V$ Input Pin CapacitanceOutput Pin Capacitance | 3.3V Supply Current at 64MHz 100 140 3.3V Supply Current at 100 MHz 150 185 3.3V Supply Current in Three-State 5 5 Input Low Voltage V _{SS} -0.3 5 Input High Voltage 2.0 1 Input Leakage Current, BUF_IN -5 5 Input Leakage Current ^[1] -20 5 ts (SDRAM0:9) ^[2] 0 10L = 1 mA 0 Output Low Voltage I _{OL} = 1 mA 3.1 0 Output High Voltage I _{OH} = -1 mA 3.1 100 Output High Current V _{OL} = 1.5V 70 110 Output High Current V _{OH} = 1.5V 65 100 mce/Inductance 100 100 100 100 | 3.3V Supply Current at 64MHz 100 140 180 3.3V Supply Current at 100 MHz 150 185 220 3.3V Supply Current in Three-State 5 10 10 140 180 Input Low Voltage 5 10 5 10 Input Low Voltage 2.0 V_{SS} -0.3 0.8 Input High Voltage 2.0 V_{DD} +0.5 Input Leakage Current, BUF_IN -5 +5 Input Leakage Current ^[1] -20 +5 ts (SDRAM0:9) ^[2] 0 I_{OL} = 1 mA 50 Output Low Voltage I_{OL} = 1 mA 3.1 0 Output Low Current V_{OL} = 1.5V 70 110 185 Output Low Current V_{OH} = 1.5V 65 100 160 nce/Inductance 150 5 100 160 |

Notes:

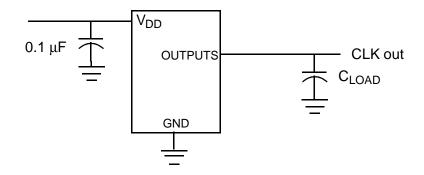
1. OE, SDATA, and SCLOCK logic pins have a 250-k Ω internal pull-up resistor (V_{DD} – 0.8V). 2. All SDRAM outputs loaded by 6" transmission lines with 22-pF capacitors on ends.



AC Electrical Characteristics: $T_A = -40$ °C to +85 °C, $V_{DD} = 3.3$ V±5% (Lump Capacitance Test Load = 30 pF)

| Parameter | Description | Test Condition | Min. | Тур. | Max. | Unit |
|------------------|--------------------------------|----------------------------|------|------|------|------|
| f _{IN} | Input Frequency | at 64 MHz | 0 | | 133 | MHz |
| t _R | Output Rise Edge Rate | Measured from 0.4V to 2.4V | 1.5 | | 4.0 | V/ns |
| t _F | Output Fall Edge Rate | Measured from 2.4V to 0.4V | 1.5 | | 4.0 | V/ns |
| t _{SR} | Output Skew, Rising Edges | | | | 200 | ps |
| t _{SF} | Output Skew, Falling Edges | | | | 200 | ps |
| t _{EN} | Output Enable Time | | 1.0 | | 8.0 | ns |
| t _{DIS} | Output Disable Time | | 1.0 | | 8.0 | ns |
| t _{PR} | Rising Edge Propagation Delay | | 3.0 | 3.85 | 5.0 | ns |
| t _{PF} | Falling Edge Propagation Delay | | 3.0 | 3.85 | 5.0 | ns |
| t _D | Duty Cycle | Measured at 1.5V | 50 | | 60 | % |
| Zo | AC Output Impedance | | | 15 | | Ω |

Test Circuit

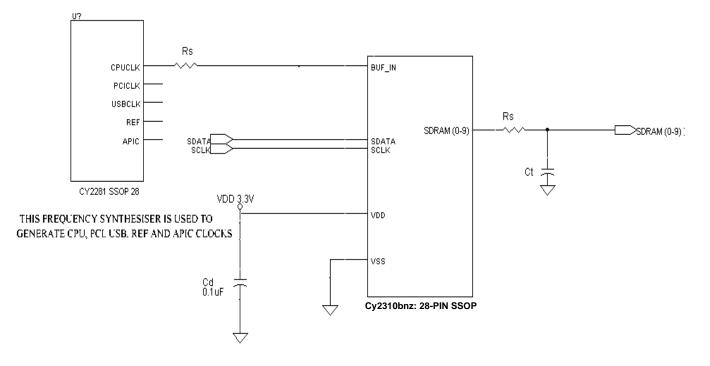




Application Information

Clock traces must be terminated with either series or parallel termination, as they are normally done.

Application Circuit



Cd = DECOUPLING CAPACITOR

- Ct = OPTIONAL EMI-REDUCING CAPACITORS
- Rs = SERIES TERMINATING RESISTORS

Summary

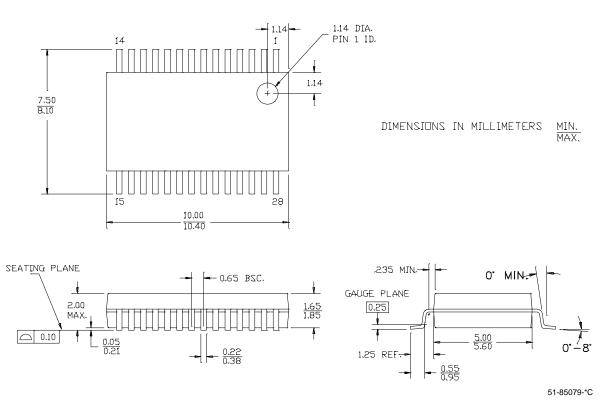
- Surface mount, low-ESR, ceramic capacitors should be used for filtering. Typically, these capacitors have a value of 0.1 μF. In some cases, smaller value capacitors may be required.
- The value of the series terminating resistor satisfies the following equation, where Rtrace is the loaded characteristic impedance of the trace, Rout is the output impedance of the buffer (typically 25W), and Rseries is the series terminating resistor. Rseries > Rtrace – Rout
- Footprints must be laid out for optional EMI-reducing capacitors, which should be placed as close to the terminating resistor as is physically possible. Typical values of these capacitors range from 4.7 pF to 22 pF.
- A Ferrite Bead may be used to isolate the Board V_{DD} from the clock generator V_{DD} island. Ensure that the Ferrite Bead offers
 greater than 50W impedance at the clock frequency, under loaded DC conditions. Please refer to the application note "Layout
 and Termination Techniques for Cypress Clock Generators" for more details.
- If a Ferrite Bead is used, a 10 μF–22 μF tantalum bypass capacitor should be placed close to the Ferrite Bead. This capacitor prevents power supply droop during current surges.



Ordering Information

| Ordering Code | Package Name | Package Type | Operating Range |
|----------------|-----------------|--------------|---|
| CY2310BNZPVI-1 | O28 | 28-pin SSOP | Industrial (-40 to 85 ⁰) |

Package Diagram



28-Lead (5.3 mm) Shrunk Small Outline Package O28

Document #: 38-07260 Rev. **

© Cypress Semiconductor Corporation, 2001. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress Semiconductor product. Nor does it convey or imply any license under patent or other rights. Cypress Semiconductor does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress Semiconductor against all charges.



| Document Title: CY2310BNZ 3.3V SDRAM Buffer for Mobile PCs with 4 SO-DIMMS Document Number: 38-07260 | | | | | |
|---|---------|---------------|--------------------|---|--|
| REV. | ECN NO. | Issue Date | Orig. of Change | Description of Change | |
| ** | 110525 | 02/07/02 | SZV | Change from Spec number: 38-01089 to 38-07260 | |